Inkjet-Printing-Based Soft-Etching Technique for High-Speed Polymer Ambipolar Integrated Circuits

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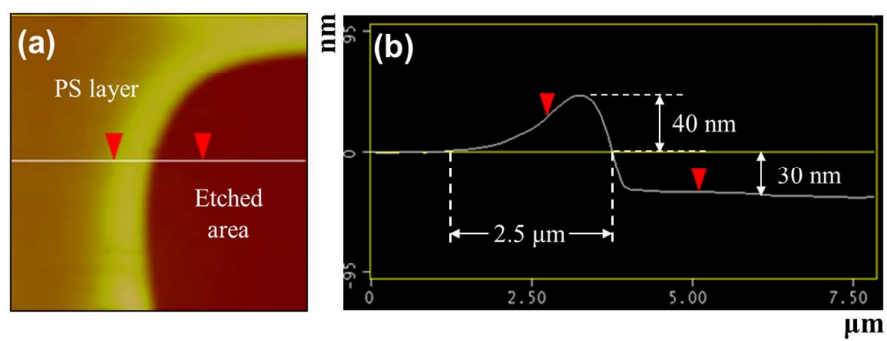
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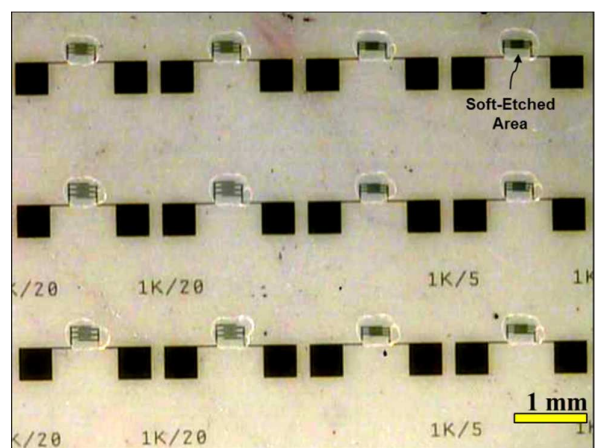
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Figure S1. (a) AFM image of soft-etched PS area on P(NDI2OD-T2) layer. (b) Corresponding cross-sectional image.

Figure S2. Optical microscope image of a PS soft-etched transistor array on a glass substrate.

Figure S3. Field-effect mobility for ambipolar P(NDI2OD-T2) semiconductors with various gate dielectric layers. The values of μ_{FET} and V_{Th} were calculated at the saturation regime ($V_d = \pm30$ V) using gradual channel approximation equations (W/L = 1.0 mm/20 μm).